TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT15J311, GT15J311(SM)

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

• Third-generation IGBT

Enhancement mode type

• High speed : $t_f = 0.30 \mu s$ (Max.) ($I_C = 15A$) • Low saturation voltage : V_{CE} (sat) = 2.7V (Max.) ($I_C = 15A$)

• FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

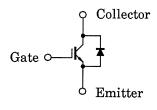
CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Collector Current	DC	Ic	15	Α	
	1ms	I _{CP}	30	Α	
Emitter-Collector	DC	lF	15	Α	
Forward Current	1ms	I _{FM}	30	Α	
Collector Power Dissipation (Tc = 25°C)		P _C	70	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	

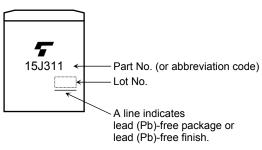
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit Marking





1. GATE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC

JEITA

TOSHIBA

2.3MAX

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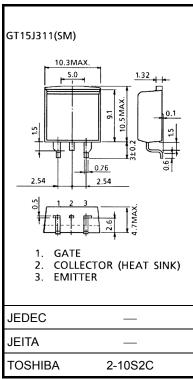
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Unit: mm

Weight: 1.5 g (typ.)



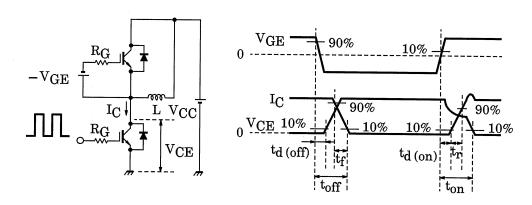
Weight: 1.4 g (typ.)



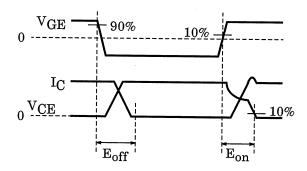
Electrical Characteristics (Ta = 25°C)

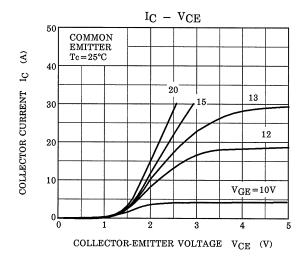
CHARA	CTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	V _{GE} =±20V, V _{CE} = 0	_	_	±500	nA
Collector Cut-Off Current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-Emitter Cut-Off Voltage		V _{GE} (OFF)	I _C = 1.5mA, V _{CE} = 5V	5.0	_	8.0	V
Collector-Emitter S	Saturation Voltage	V _{CE} (sat)	I _C = 15A, V _{GE} = 15V	_	2.1	2.7	V
Input Capacitance		C _{ies}	V _{CE} = 20V, V _{GE} = 0, f = 1MHz	_	950	_	pF
Switching Time	Rise Time	t _r	Inductive Load V_{CC} = 300V, I_{C} = 15A V_{GG} = ±15V, R_{G} = 75 Ω (Note 1)	_	0.12	_	- μs
	Turn-On Time	t _{on}		_	0.40	_	
	Fall Time	t _f		_	0.15	0.30	
	Turn-Off Time	t _{off}		_	0.50	_	
Peak Forward Voltage		V _F	I _F = 15A, V _{GE} = 0	_	_	2.0	V
Reverse Recovery Time		t _{rr}	I _F = 15A, di / dt = -100A / μs	_	_	200	ns
Thermal Resistance (IGBT)		R _{th (j-c)}	_	_	_	1.79	°C/W
Thermal Resistance (Diode)		R _{th (j-c)}	_	_	_	3.45	°C/W

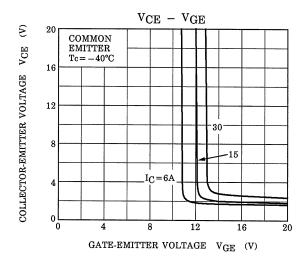
Note 1: Switching time measurement circuit and input / output waveforms

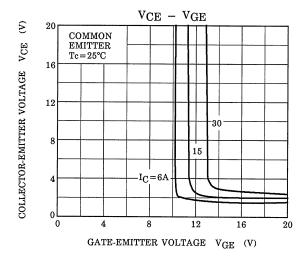


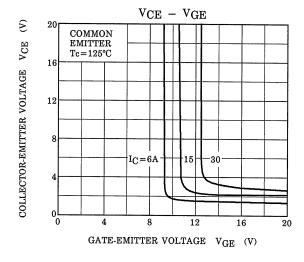
Switching loss measurement waveforms

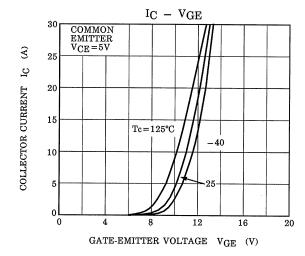


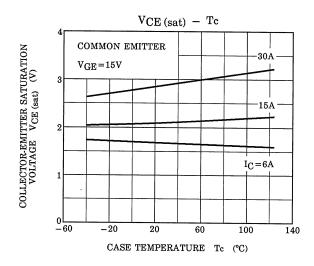




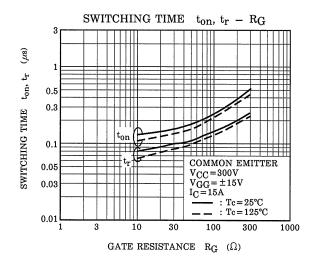


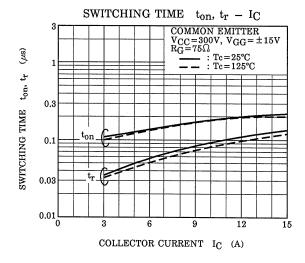


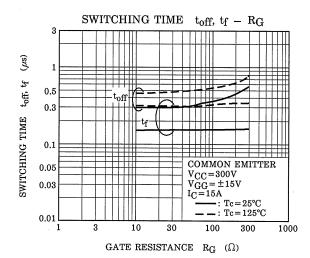


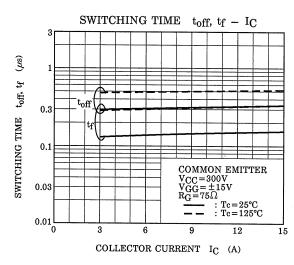


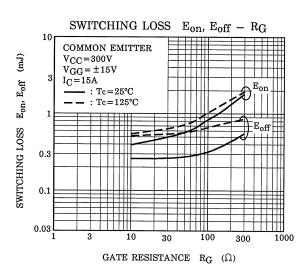
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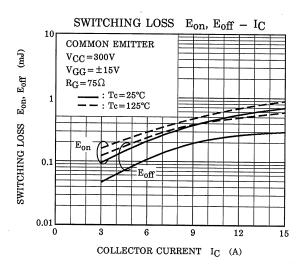


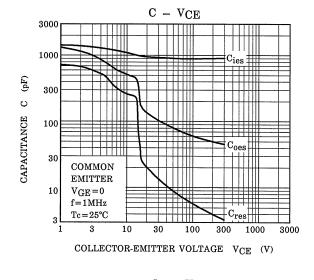


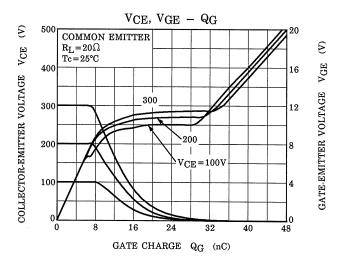


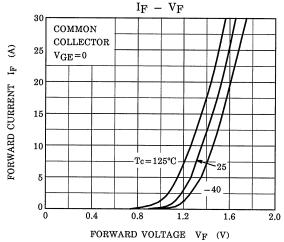


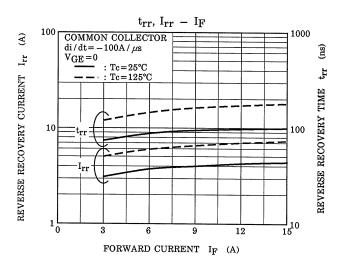


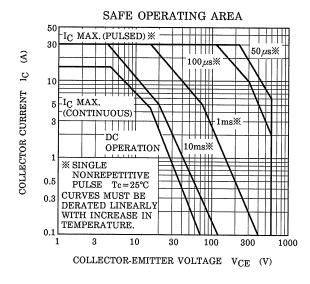


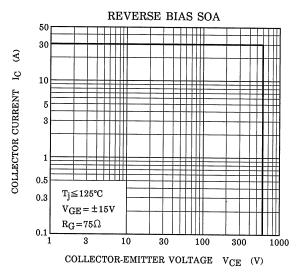




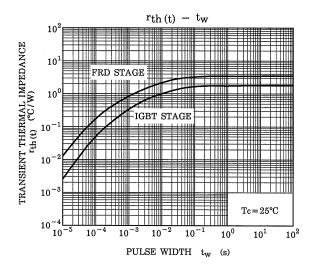








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